Creating Catalyst-containing Nanostructures via Self-assembled Block Copolymer Templates for Rationally Synthesis of 1D nanostructures

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# **Carbon Nanotubes**

### **Excellent mechanical properties: Composite**

100 to 200 times stronger than steel

#### **Excellent electron transport property: Transistors**

- $\mu~\sim$  3000 to 20,000 cm²/V-sec max reported in p-type CNTFETs
- $\mu \sim 500 \text{ cm}^2/\text{V-sec Si-pFETs}$

### High aspect ratio, huge current capability: Field emission tips

 $CNT: 10^{9}A/cm^{2} \quad Metal: < 10^{6}A/cm^{2} \quad Si: < 10^{3}A/cm^{2}$ 



Space cable (NASA)



**CNTFET(IBM)** 



**CNT-based X ray (UNC)** 

### Nanowires

#### **Electronic based sensor Multiplexed electrical detection of cancers** 2 3 5 6 2,100 1,950 1,800 1,650 **PSA** NW1 (Prostate) NW2 CEA (Intestinal) 1,650 -NW3 mucin-1 (Overian and Breast) 1,500 2,000 4,000 8,000 6.000 0 G. Zheng, F. Patolsky, Y. Cui, W.U. Wang, C.M. Lieber, Nat. Biotechnol., 23, 1294 (2005)

Nano-electricity

Z.L. Wang Georgia Tech

<sup>5µm</sup>ZnŎ

generators

m٧

NanoLaser

Perform Laser surgery

X. Duan, Y. Huang, R.Agarwal. C.Lieber. Nature 421, 241-245 (2003)

# Challenges

### Lack of <u>controllable synthesis</u> prevents realizing their highly touted properties



Location and diameter are determined by catalyst

### Challenges

Controllable growth  $\rightarrow$  Catalysts with <u>controlled size and spacing at predefined locations</u>

Transition metal

Carbon nanotubes: Fe, Co, Ni

Nanowires:Au: InP, InAlAs, GaN, SiNi: GaN, SiC, Si

 $\leq$  3 nm for single-walled carbon nanotubes Catalyst nanoparticle size  $\leq$  20 nm for nanowires

Current top-down lithography

Self-assembled block copolymer



Background: Block copolymers

• Iron-containing nanostructures for CNT growth

Thin film self-assembled iron-containing block copolymers

• Catalytically active transition nanoparticles for CNT and Si nanowire growth Solution self-assembled metal modified block copolymers

Conclusion

### Outline

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# Nanomorphologies Produced by Diblock Copolymer



Self-organize metal-containing block copolymer to produce metal-based nanostructures (A) with periodic size and spacing surrounded by (B)



Template for generating metal-containing nanostructures

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# Iron-containing Ferrocenylsilane Block Copolymers Iron is a well-known catalyst system for CNT growth



### **Thin film Self-assembled Morphologies**



Ø <sub>PFS</sub>	PS	PFS	Domain size	Spacing
0.33	253	44	14	28
0.25	402	98	22	36
0.36	389	108	31	45

Size and spacing can be adjusted by chain lengths



# **Iron-Containing Nanostructures for CNT growth**

#### Self-assembled polymer thin film

Fe-containing silica posts







Carbon nanotube uniformly distributed over a large surface area!

AFM and Raman analysis:
1 nm in diameter on average
very few defects in CNTs

Acc∀ SpotMagn Det WD Exp \_\_\_\_\_ 2 μm 1.00 KV 3.0 8000x TLD 6.0 0

### Si Rich Ferrocenylsilane-based Copolymer Systems



SiO<sub>2</sub> may further reduce aggregation SiO<sub>2</sub> Spacer Oxygen plasma

#### PMVS<sub>377</sub>-b-PFEMS<sub>25</sub> (13vol% PFEMS)

#### AFM height image

1 μm by 1 μm scan 10 nm in height

# SEM image

 $4~\mu m$  by  $4~\mu m$ 







# **Tailoring CNTs by Adjusting Block Lengths**



Tailoring polymer chain lengths → Fe-containing nanostructure size & density → CNT diameter & density

**Rationally synthesize CNTs with predictable and tunable size and density** 

 $PMVS_{377}$ -b-PFEMS<sub>25</sub> G/D= 6 (1.1 nm)  $PMVS_{837}$ -b-PFEMS<sub>45</sub> G/D= 12 (1.6 nm)

Growth condition for producing defect-free CNTs is sensitive to catalyst size.

# **CNTs for Display Application**



#### Display Market: \$50 billion per annum

- Thinner
- Brighter
- Better color reproduction
- Faster response time
- Lower power consumption

#### **Few-walled CNTs**

Excellent field emission properties
Superior mechanical integrity

Directly grow uniform upright few-walled CNTs on ITO coated glass



# **CNTs for Display Application**

Catalyst: Fe-containing nanostructures (PS<sub>389</sub>-b-PFEMS<sub>108</sub>) Carbon nanotube growth condition: PECVD, 600°C









#### **Excellent Field emission!**

#### **<u>PS-b-PFEMS block copolymer template</u>**:

Tailoring block lengths

Upright few-walled CNTs→ Excellent emission properties

Uniformly dispersed catalyst species

Evenly populated CNTs — Uniform emission

### **Selective Growth of CNTs**

#### **Combination of top-down litho with bottom-up self-assembly**



#### Self-assembly and lithography patterning processes on a 3 inch wafer format

### **Diameters of CNTs Grown from Catalyst Islands**



Majority of tubes have diameters around or less than 1nm

# **Conventional Transistor Design** Either directly growing CNTs or dispensing as-synthesized CNTs, electrical contact is a random event! not manufacturable process!



### **Circular Transistor Design**



• Weighted average of many tubes ----> Greatly improve consistency and predictability Increase current carrying capacity and gm •

• Diameter and chiral arrangement Alleviate requirements Orientation • Length

# **Selective Growth of Suspended CNTs**



Suspended tubes are free of interaction with underlying substrates

Characterize CNTs by optical means

### **Raman Characterization**



### **Selective Growth of Suspended CNTs**



Suspended tubes are free of interaction with underlying substrates

Characterize CNTs by optical means
 <u>Ideal p-n junction diode (GE)</u>
 <u>Greatly enhanced IR emission (IBM)</u>

Nanoelectromechnical applications <sup>-</sup>

Ultra-sensitive Mechanical Sensor Mechanical perturbation induces change in resistance Nano-mechanical Switch CNTs mechanically deflected to establish electrical contact Nano-oscillator

Block copolymer  $\rightarrow$  controllable synthesis suspended CNTs  $\rightarrow$  facilitate device applications

### Summary: Thin film self-assembled <u>Ferrocenylsilane-based Block Copolymers</u>

- Iron-containing nanostructures with precise control in size and spacing have been generated by this block template
- Tuniformly distributed and high-quality CNT mats have been produced
- **•** Selective growth of CNTs on a surface or in suspension has been demonstrated
- ➤ CNTs with diameters ~1 nm
- Few-walled, upright CNTs have been synthesized at 600°C with excellent emission properties
- **~** CNT's size and density can be adjusted by tailoring block lengths

For a given growth condition, the amount of dangling bonds varies with catalyst size. To achieve defect-free CNTs with consistent properties, it is essential to have uniform sized catalytically active nanostructures.



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# **PS-b-P2VP:Metal-induced Micellization**





# **Solution Self-assembly: Various Metal Nanoparticles**



#### AFM height images:10 nm in Z scale, 1 by 1µm scan

# **CNT Mats**



High quality CNTs and uniformity maintained over a large surface area

Growth mechanism: Effect of catalyst composition

Ni

### **Tuning Size & Spacing**



3.3 nm, 49 nm

**PS<sub>475</sub>-b-P2VP<sub>141</sub>** 2.6nm, 45 nm

PS<sub>2128</sub>-b-P2VP<sub>539</sub>

3.8 nm, 140 nm

7.5 nm, 81 nm

Size and spacing dictated by block lengths

4.2 nm, 70 nm

AFM height images 1 by 1µm scan

### **Narrowing Spacing by Adjusting Solution Concentration**

0.5 wt % PS<sub>475</sub>-b-P2VP<sub>141</sub>

1.0 wt % PS<sub>475</sub>-b-P2VP<sub>141</sub>



#### An array of closely packed cobalt nanoparticles to promote vertically oriented CNTs can be formed!

AFM height images 1 by 1µm scan

# **CNT Diameter Control**



#### Catalyst nanoparticles do not agglomerate at high growth temperature



# **CNT 2D film**

#### PS<sub>475</sub>-b-P2VP<sub>141</sub>







	Nanoparticle size (nm)	CNT diameter (nm)
PS <sub>475</sub> -b-P2VP <sub>141</sub>	2.2 (±0.1)	1.1(±0.4)
PS <sub>794</sub> -b-P2VP <sub>139</sub>	3.8 (±0.2)	1.7(±0.5)

Electronic signal: Average properties of the individual CNTs Only density matters!

**Controlled by the block copolymer approach** 

- Thin-film transistor (high carrier mobility)
- Sensor
- MALDI-MS target

# MALDI-MS

MALDI(Matrix Assisted Laser Desorption and Ionization)

is a technique for ionization of large molecules for Mass Spectroscopic detection



Biopolymer is dissolved in a solvent

Matrix molecule is added (e.g. trans-cinnamic acid, 10,000 times more than biopolymer).

UV-Laser causes the disintegration of matrix

Evaporation and ionization of biopolymers

Positively charged fragmented ions are accelerated and detected

# **Carbon Nanotube Coated Surface as MALDI Target**

#### 500 attomoles BSA (bovine serum albumin) in 0.25 mg/mL CHCA matrix



Able to identify 500 attomoles of bovine serum albumin using CNT surfaces

# **Catalyst Support**



#### Fail to reduce to 0

	SiO <sub>2</sub>	Mo	$Si_3N_4$
CNT	dense, long, small	sparse, short , large	No CNTs
Fe Before growth	0.53% (+3)	0.56% (+3)	0.52% (+3)
Fe After growth	0.21% (0)	< 0.1%(0)	< 0.1%(+2, +3)

Fe nanoparticles adhere poorly on Mo and  $Si_3N_4$  surfaces

**Growth mechanism: Effect of catalyst support** 

### **Growth Mechanism: Carbon feed rate**



Collaboration with Duke

### **Lithographic Selective Growth**



#### Patterned PS-b-CoPVP

Selective growth of CNTs over a large surface area!

### **CNT Growth Results**



### **Electrical Test Results**

#### Optical lithography to define catalyst nanostructure arrays on a wafer format

CNT growth J Source and Drain

Resistance is 30 kΩ at zero bias
>7 μA pass through

Decent tubes
Good metal contact



3 inch process! However, tube density is extremely low!

Wafer level processing for fabricating CNT- based electronics

### Summary: Solution Self-assembled <u>PS-b-PVP Micelles</u>

- Highly ordered nanoparticles with tunable composition, size and spacing on various surfaces can be produced
- Uniformly distributed and high-quality CNT mats have been obtained
- **~** CNTs with diameters ~ 1 nm have been synthesized using Co nanoparticles
- **>** Selective growth of CNTs on a surface or in suspension has been demonstrated
- **•** Wafer-level fabrication of CNT-based electronic devices has been established

### **Provide an opportunity of studying the growth mechanism** Catalyst composition Catalyst support Carbon stock feed rate

# Silicon Nanowires from Au Nanoparticles

Au nanoparticles: 5 nm

PS<sub>475</sub>-b-P2VP<sub>141</sub> HAuCl<sub>4</sub>

AFM height images 1 by 1µm scan, 10 nm in height











(20~80 nm from catalyst breaking up 1 nm Au thin film)



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### **Important Attribute of Block Copolymer Template**

#### Nano

Size and Spacing: Mw of each segment Number of metal atoms incorporated onto a polymer chain

#### Micro and sub-micro

Lithography

#### Macro

Superior film forming capability serves as a carrier to uniformly distribute nanostructures across a wafer

Ability to control at nano-, micro- and macro-scales simultaneously

**Controllable synthesis of 1D nanostructures on a wafer format** 

**Fully compatible with existing semiconductor processes** 

### Conclusion

Thin film self-assembly Ferrocenylsilane-based diblock copolymer

> Solution self-assembly Various metal-complexed PS-b-PVP

Metal-containing nanostructures with controllable and tunable size, spacing and composition

CNTs and Si nanowires: uniform density, narrow diameter distribution, spatially controlled

**Predictable and reproducible nanofabrication method** 

<u>Applications:</u> Transistor, Display, MALDI-MS targets, NEMS

Catalyst size Understanding growth mechanism: Catalyst support Carbon stock feeding rate **Current Collaborators** 

<u>University of Toronto</u> Prof. Mitch Winnik

David Rider

<u>Duke University</u> Prof. Jie Liu Chen Qian

Bristol University Prof. Ian Manners <u>MIT</u> Prof. Mildred Dresselhaus Hyungbin Son

<u>University of North Carolina at Chapel Hill</u> Prof. Otto Zhou Eric Peng Thanks you!